Electronic supplementary information

A Robust and Low-Cost Strategy to Prepare Cu_2ZnSnS_4 Precursor Solution and Its Application in $Cu_2ZnSn(S,Se)_4$ Solar Cells

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Figure S1. A digital photograph of graphite box.

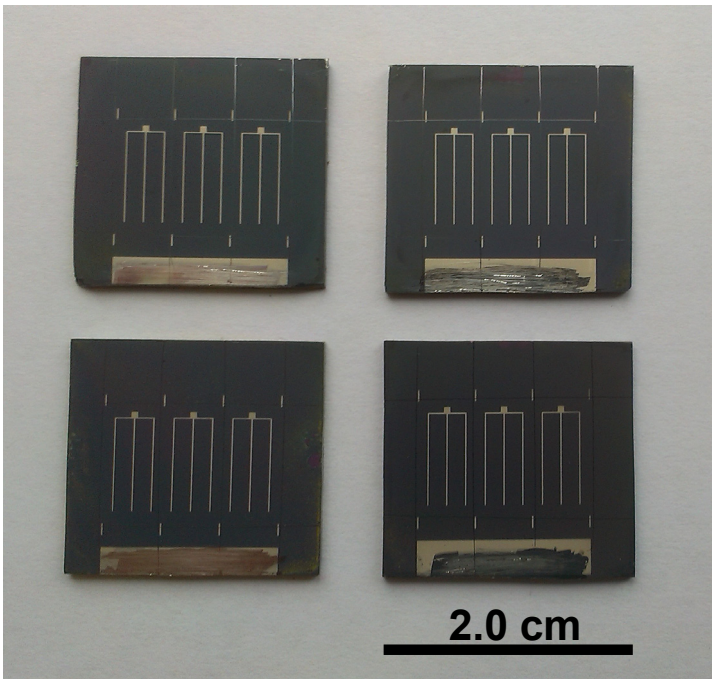

Figure S2. A digital photograph of CZTSSe solar cells.

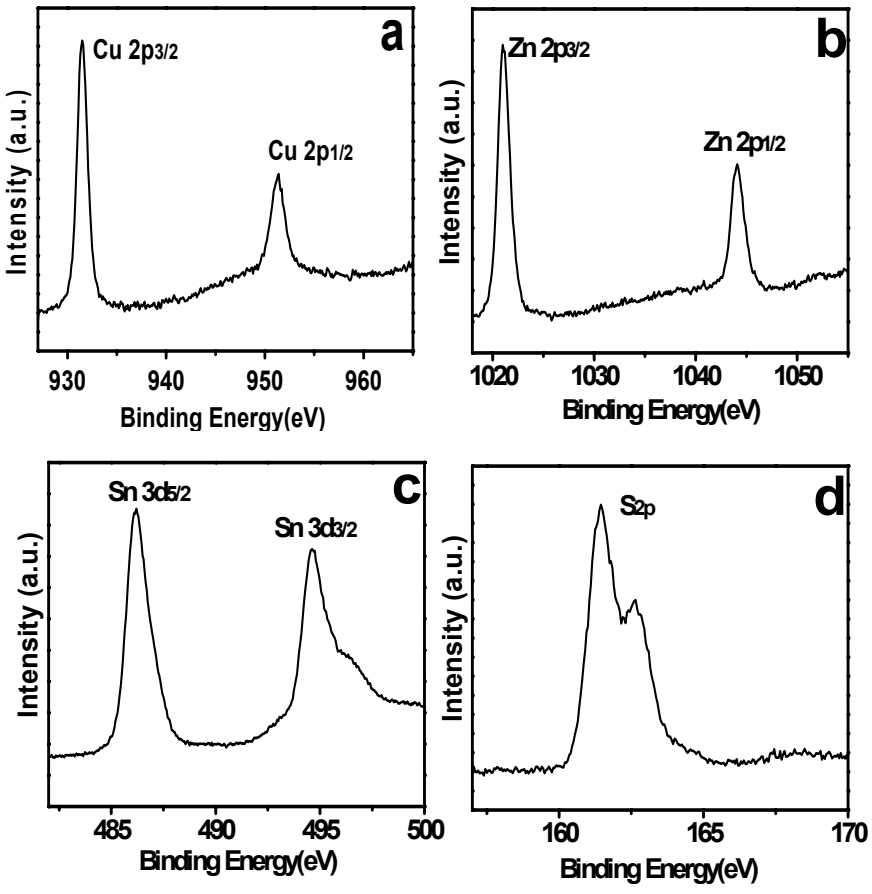

Figure S3. XPS spectra of the as-fabricated CZTS thin film.

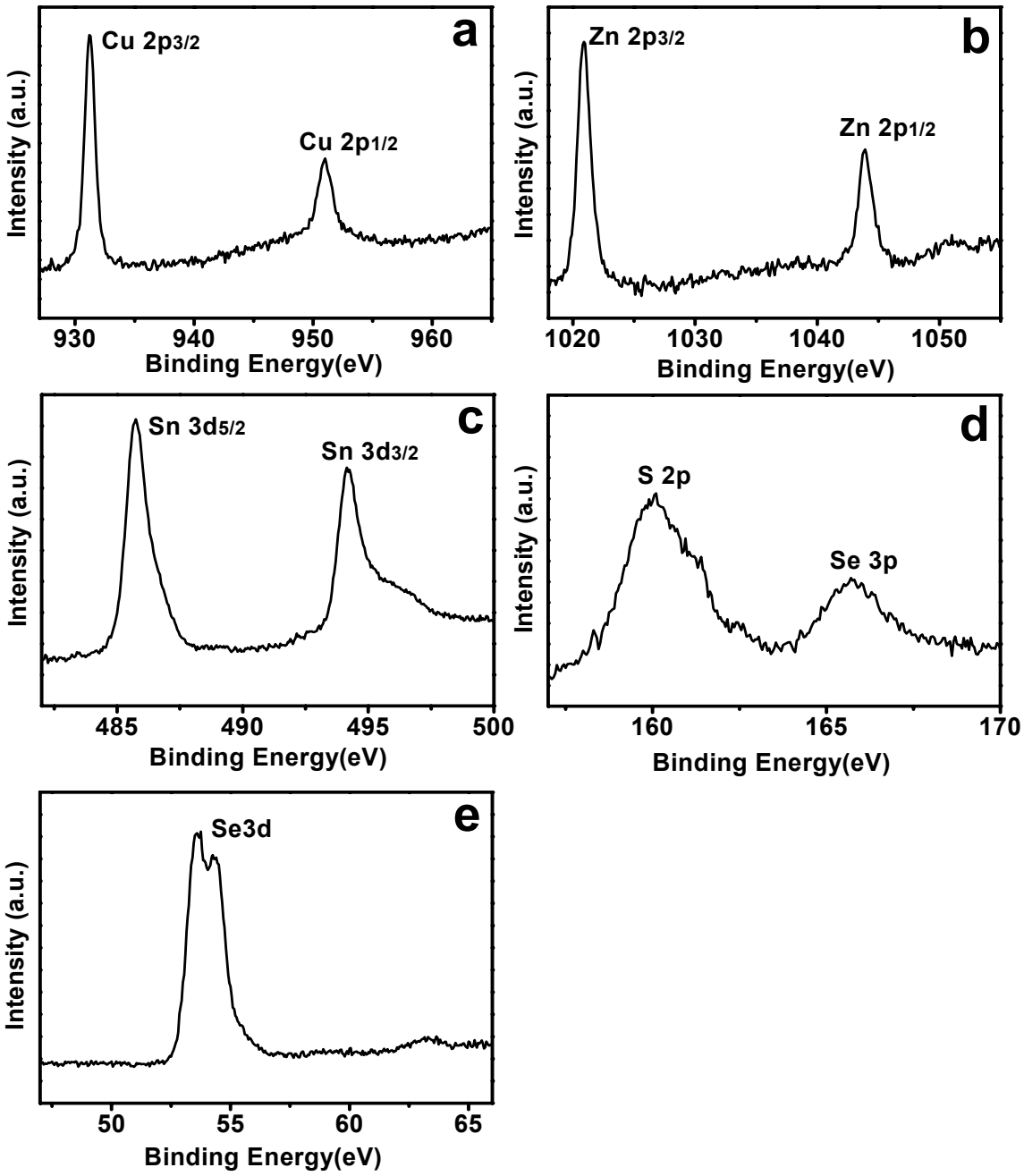

Figure S4. XPS spectra of the selenized CZTSSe thin film.

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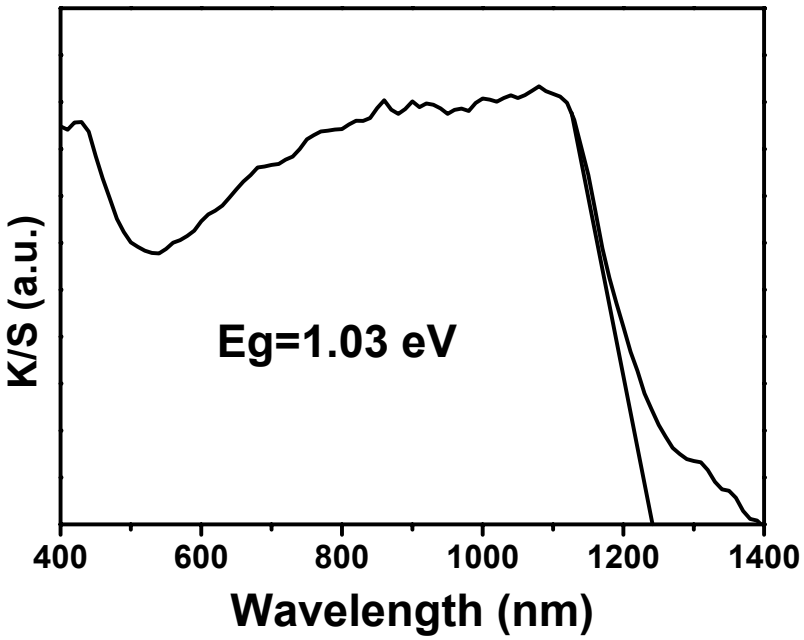

Figure S5. The band gap of selenized CZTSSe thin film was calculated by extrapolating the Kubelka-Munk function to K/S=0.